Features

- Wide range of operating voltage: 1.6V to 5.5V
- Low crystal drive current oscillation for miniature crystal units
- XO5052C/B series: for Wire Bonding
  - XO5052Cx : C type package
  - XO5052Bx: B type package(2016)
- -45 to +125℃ operating temperature range
- Crystal frequency (10MHz~60MHz)
- Output Freq: Crystal Freq divided by 1/2/4/8/16
- Very low standby current
- 50±5% output duty cycle
- 50pF output drive capability（2.25~5.5V）
- 15pF output drive Capability (1.6~2.25V)
- Die form or Wafer form

Applications

- Fundamental Crystal Oscillator
- 7050, 5032, 3225, 2520, 2016 crystal oscillator

Description

The XO5052 series are miniature crystal oscillator module ICs. The oscillator circuit stage has constant current drive, significantly reducing current consumption and crystal current, compared with existing devices, and significantly reducing the oscillator characteristics supply voltage dependency.

Ordering Information

Part no.	Package type
XO5052xy-zWF	Wafer form
XO5052xy-zDE	Die form

Note 1: x: B suitable for B Base, C suitable for C base
Note 2:.y: 1/2/3/4(1//2/4/8/16)
Note 3: z: -8(180um) or -3(130um), -4(100um)

XO 5052 C 1

Device Type
OSC IC

XO 5052 Series

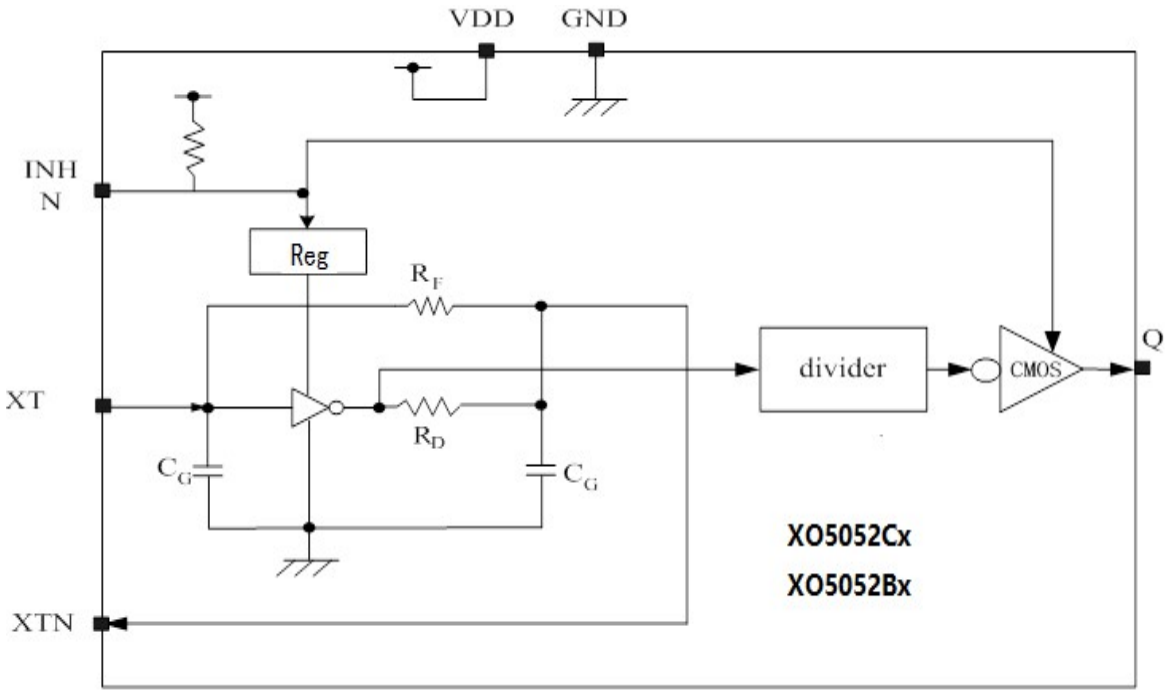
Pad layout type

B: for Wire Bonding(type I)
C: for Wire Bonding(type II)

Oscillation frequency range, frequency divider function

Suffix	foutput	Frequency range
1	fo	10 to 60MHz
2	fo/2	
3	fo/4	
4	fo/8	
5	fo/16	
6	fo/32	
7	fo/64	
8	fo/128	
9	fo/256	

Block Diagram



Function Description

Standby Function

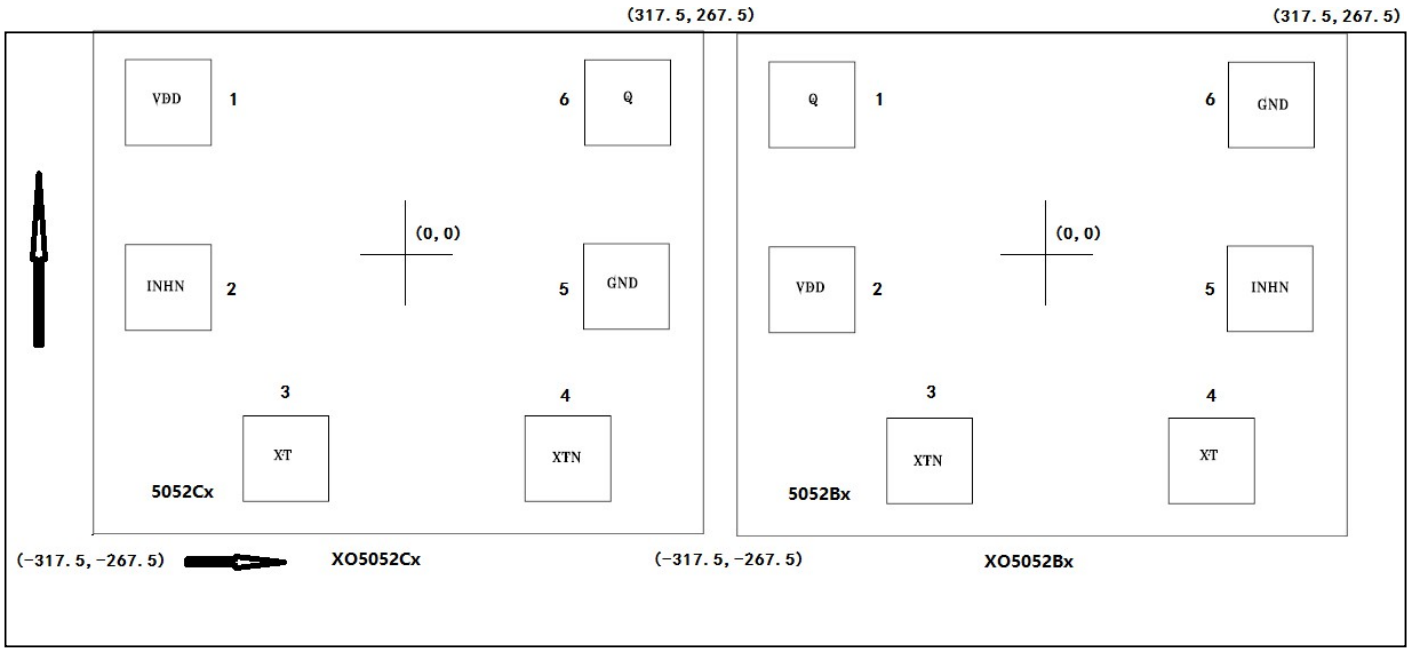
When INHN goes LOW, the oscillator stops and the output on Q becomes high impedance.

INHN	Q	Oscillator
HIGH (or open)	F0/1/2/4/8/16 output frequency	Normal operation
Low	High impedance	Stopped

Power-saving Pull-up Resistor

The INHN pin pull-up resistance RUP1 or RUP2 changes in response to the input level(HIGH or LOW). When INHN is tied LOW level, the pull-up resistance is large(RUP1),reducing the current consumed by the resistance. When INHN is left open circuit, the pull-up resistance is small(RUP2),which increases the input susceptibility to external noise. However, the pull-up resistance ties the INHN pin HIGH level to prevent external noise from unexpectedly stopping the output.

Pad Configuration



Pad Coordinate File					
Pad Name	X Coordinate	Y Coordinate	Pad Name	X Coordinate	Y Coordinate
1	-214.85	168	4	158.35	-164.6
2	-214.85	-4.65	5	213.15	-3.85
3	-105.1	-164.6	6	214.2	167.9
Note: Substrate is connected to GND or floating.					
Die Size: 630μm*530μm (Including scribe line , Scribe Line Width 60um) **Die Thickness:** 130μm±15μm(-3) or 180um±20um(-8), 220um±20um(-2), 100um±15um(-4) **Pad Size:** 80μm*80μm **Substrate Level:** GND or Floating					

Pad Description

Sym.	Type	Description	
XTN	O	Amplifier output.	Crystal oscillator connected between XT and XTN
XT	I	Amplifier input.	
INHN	I	Output state control input. Output High when LOW. Power-saving pull-up resistor built in.	
V_{DD}	P	Supply voltage	
GND	P	Ground	
Q	O	Output. Output frequency determined by fundamental crystal(f0 divided by 1/2/4/8/16/..)	

Maximum Ratings

Symbol	Parameter	Min	TYP	Max	Unit
T_{store}	Storage Temperature	−65	-	+150	°C
V_{DD}	Supply Voltage Range	-0.5	-	7.0	V
V_{IN}	Input Voltage Range	-0.5	-	V_{DD}+0.5	V
V_{OUT}	Output Voltage Range	-0.5	-	V_{DD}+0.5	V
I_{OUT}	DC Output Current (Q output)	-	-	20	mA

Notes:
Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Recommended Operating Conditions

(GND=0V, unless otherwise noted.)

Sym.	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	Supply voltage	-	1.6	-	5.5	V
T_A	Operating temperature	-	-45		+125	°C
f_0	Oscillation frequency*1	-	10		60	MHz

DC Electrical Characteristics

XO5052(V_{DD} = 1.6 to 5.5V, T_A = -40 to 85°C, unless otherwise noted.)

Parameter	Sym	Conditions		Min	Typ	Max	Unit
HIGH-level output voltage	V_{OH}	I_{OH}=1mA		V_{DD}-0.4	-	-	V
LOW-level output voltage	V_{OL}	I_{OL}=1mA		-	-	0.4	
HIGH-level input voltage	V_{IH}	OE Measurement		0.7Vcc	-	-	V
LOW-level input voltage	V_{IL}	OE Measurement		-	-	0.4	
Operating current	I_{CC}	Vdd=1.8V(25MHz), no loading		-	0.65	1.3	mA
Operating Current	I_{cc}	Vdd=3.0V(25MHz), no loading		-	1.4	2.8	mA
Operating Current	Icc	Vdd=1.8V(25MHz),15pf loading		-	1.3	2.0	mA
Operating Current	Icc	Vdd=3.0V(25MHz),15pf loading		-	2.5	3.5	mA
Standby Current	Isb	OE=off				10	uA
OE pull-up resistance	R_{PULL}	V_{DD} = 3.3V		-	2	-	MΩ
Output leakage current	I_Z	OE=OFF	V_O =V_{DD}	-	-	10	μA

AC Characteristics

XO5052C/B, T_A=-40 to 85℃ unless otherwise noted

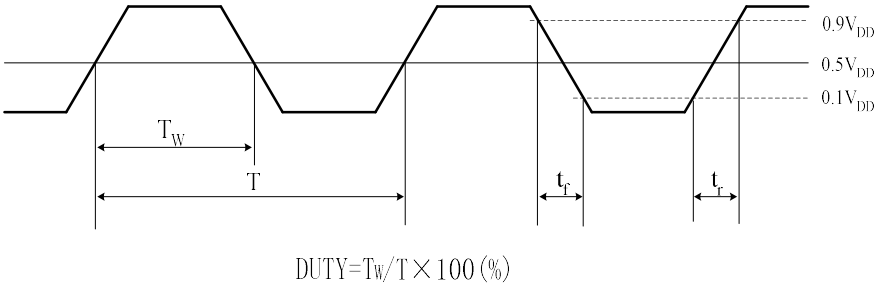
Parameter	Symbol	Condition		Min	Typ	Max	Unit
Output Disable Delay	t_{OD}	Output Disable Function (OE)		-	-	100	ns
Output Enable Delay	t_{STR}	Output Enable Function (OE)		-	-	10	ms
Output rise time	t_{r1}	C_L=15pF, 0.1V_{DD} to 0.9V_{DD}	V_{DD}=3.3V	-	1.6	2.5	ns
Output fall time	t_{f1}	C_L=15pF, 0.1V_{DD} to 0.9V_{DD}	V_{DD}=3.3V	-	1.6	2.5	ns
Output duty cycle	Duty	T_A=25°C, C_L=15pF		45	50	55	%
V_{DD} Sensitivity Frequency vs. VDD+/-10% -2 2 ppm		Frequency vs. V_{DD}+/-10%		-1.5	-	+1.5	ppm
OSC frequency range	f_R	Fundamental Crystal		20		60	MHz

Crystal Specifications

Parameters	Sym	Conditions	Min	Typ	Max	Units
Fundamental Crystal Resonator Frequency(XO5052)	F_{XIN}	-	10		60	MHz
Maximum Sustainable Drive Level		-	-	-	200	μW
Operating Drive Level		-	-	30	-	μW
Crystal Shunt capacitance	C_O	-	-	-	4	pF
Effective Series Resistance, Fundamental, 20-60MHz	ESR	-	-	-	40	Ω

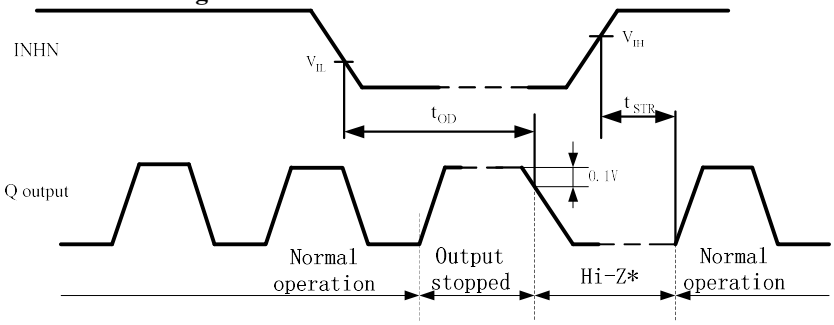
AC Electrical Characteristics

Output switching waveform



$$DUTY=T_W/T\times 100\,(\%)$$

Output disable and oscillation start timing chart

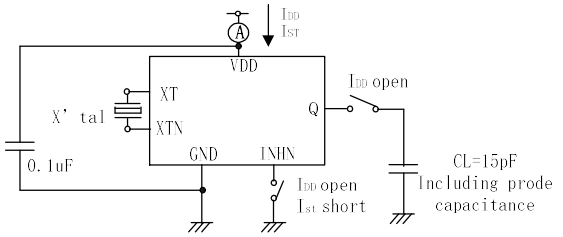


When INHN goes HIGH to LOW, the Q output goes HIGH once and then becomes high impedance.
When INHN goes LOW to HIGH, the Q output from high impedance to normal output operation when the oscillation starts (oscillation is detected)
*: the high –impedance interval in the figure is shown as a LOW level due to the 1KΩ pull-down resistor connected to the Q pin(see "Measurement circuit 2" in the "Measurement circuits" section)

Measurement Circuit

Measurement cct1

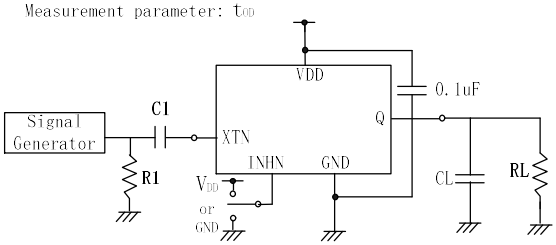
Measurement parameter: I_{DD}, I_{ST}, Duty, t_r, t_f



Note:The AC characteristics are observed using an oscilloscope on pin Q

Measurement cct2

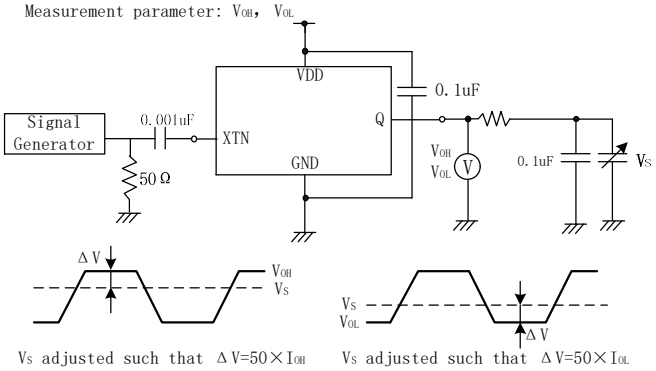
Measurement parameter: t_{OD}



XTN input signal:1Vp-p,sina wave
C1: 0.001uF CL:15pF
R1:50Ω RL: 1KΩ

Measurement cct3

Measurement parameter: V_{OH}, V_{OL}

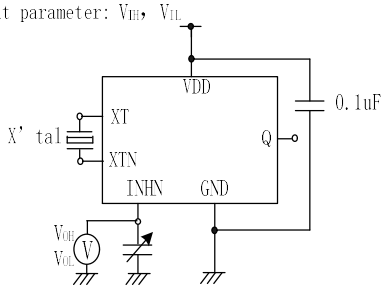


VS adjusted such that ΔV=50×IOH VS adjusted such that ΔV=50×IOL

XTN input signal:1Vp-p,sina wave

Measurement cct4

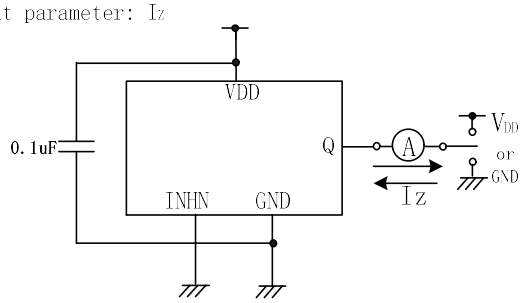
Measurement parameter: V_{IH}, V_{IL}



VIH:Voltage is 0V to VDD transition that changes the output state.
VIL:Voltage is VDD to 0V transition that changes the output state.
INHN has an oscillation stop function

Measurement cct5

Measurement parameter: Iz



Measurement cct6

Measurement parameter: R_{UP1}, R_{UP2}